

Silicon NPN Power Transistors

BUV26

DESCRIPTION

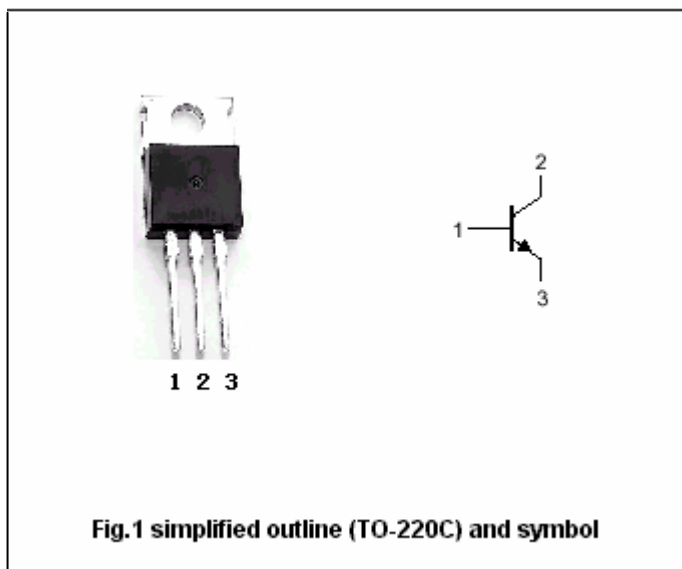
- With TO-220C package
- Low collector saturation voltage
- Fast switching speed

APPLICATIONS

- For use in high frequency and efficiency converters, switching regulators and motor control

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

Absolute maximum ratings ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	180	V
V_{CEO}	Collector-emitter voltage	Open base	90	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		14	A
I_{CM}	Collector current (peak)		25	A
I_B	Base current		4	A
I_{BM}	Base current (peak)		6	A
P_{tot}	Total power dissipation	$T_c=25^\circ\text{C}$	85	W
T_j	Max. operating junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	1.92	K/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.2 A ; I _B =0; L=25mH	90			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =6A ; I _B =0.6 A			0.6	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =12A; I _B =1.2A			1.5	V
V _{BEsat-1}	Base-emitter saturation voltage	I _C =6A ; I _B =0.6 A			1.2	V
V _{BEsat-2}	Base-emitter saturation voltage	I _C =12A; I _B =1.2A			2.0	V
I _{CEX}	Collector cut-off current	V _{CE} =180V; V _{BE} =-1.5V; T _j =125°C			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	mA

Switching times resistive load

t _{on}	Turn-on time	I _C =12A; I _{B1} =1.2A; I _{B2} =2.4A V _{CC} =50V		0.4	0.6	ms
t _s	Storage time			0.45	1.0	μs
t _f	Fall time			0.12	0.25	μs

PACKAGE OUTLINE

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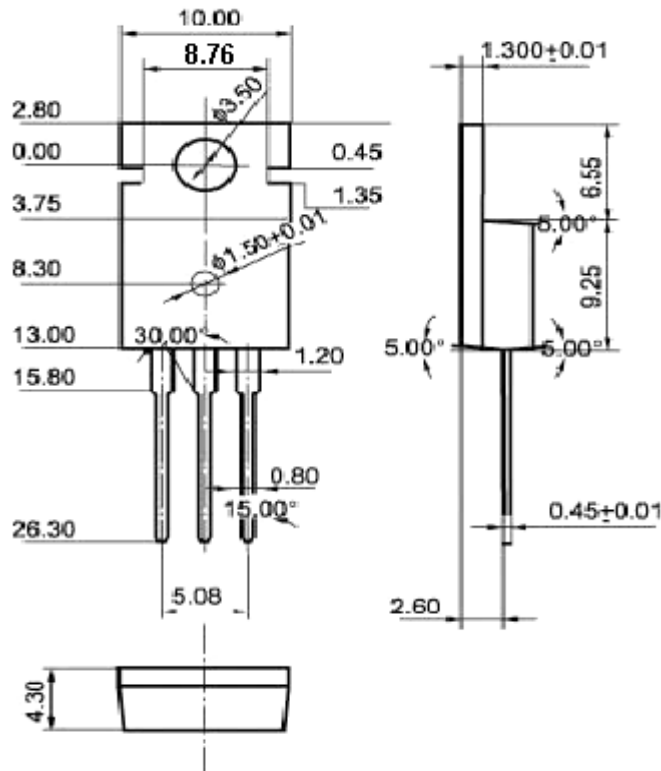


Fig.2 Outline dimensions (unindicated tolerance: 0.1mm)